





DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

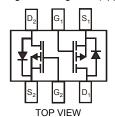
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead Free/RoHS Compliant (Note 3)
- "Green" Device (Note 5 and 6)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

SOT-363





Internal Schematic

/IEW

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-50	V
Drain-Gate Voltage (Note 1)		V_{DGR}	-50	V
Gate-Source Voltage	Continuous	V _{GSS}	±20	V
Drain Current (Note 2)	Continuous	I_{D}	-130	mA

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 2)	P _d	300	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	417	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)								
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-75	_	V	$V_{GS} = 0V, I_D = -250\mu A$		
		_	_	-15	μΑ	$V_{DS} = -50V$, $V_{GS} = 0V$, $T_{J} = 25$ °C		
Zero Gate Voltage Drain Current	Inno	_	_	-60	μA	$V_{DS} = -50V$, $V_{GS} = 0V$, $T_{J} = 125$ °C		
Zero Gate Voltage Brain Garrent	I _{DSS}	_	-	-100	nA	$V_{DS} = -25V$, $V_{GS} = 0V$, $T_{J} = 25^{\circ}C$		
Gate-Body Leakage	I _{GSS}			±10	nΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 4)								
Gate Threshold Voltage	V _{GS(th)}	-0.8	-1.6	-2.0	V	$V_{DS} = V_{GS}$, $I_D = -1mA$		
Static Drain-Source On-Resistance	R _{DS (ON)}	_	6	10	Ω	$V_{GS} = -5V, I_D = -0.100A$		
Forward Transconductance	g FS	0.05	_	_	S	$V_{DS} = -25V, I_D = -0.1A$		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{iss}	_	_	45	pF			
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1.0MHz$		
Reverse Transfer Capacitance	C _{rss}	_	_	12	pF			
SWITCHING CHARACTERISTICS								
Turn-On Delay Time	t _{D(ON)}	_	10	_	ns	$V_{DD} = -30V$, $I_{D} = -0.27A$,		
Turn-Off Delay Time	t _{D(OFF)}	_	18	_	ns	$R_{GEN} = 50\Omega$, $V_{GS} = -10V$		

Notes:

- $1. \quad R_{GS} \leq 20 K \Omega.$
- 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. No purposefully added lead.
- Short duration pulse test used to minimize self-heating effect.
- 5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 6. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.



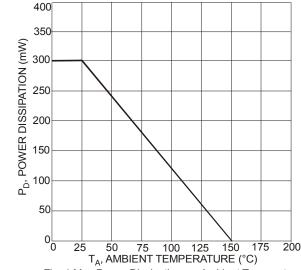
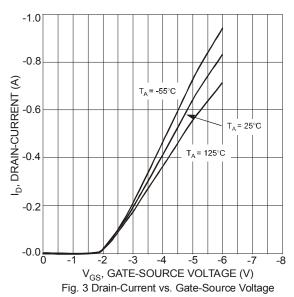
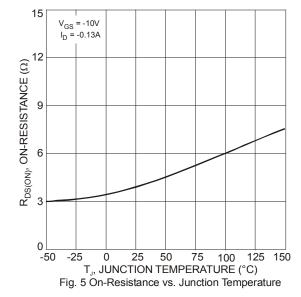


Fig. 1 Max Power Dissipation vs. Ambient Temperature





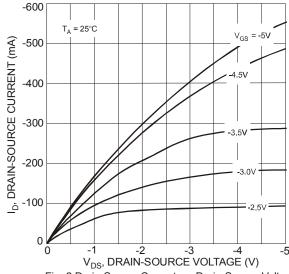
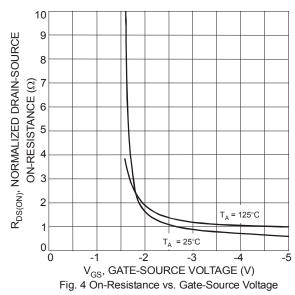


Fig. 2 Drain-Source Current vs. Drain-Source Voltage



25.0 20.0 R_{DS(ON)}, ON-RESISTANCE (Ω) = -3.5V = -3V 15.0 5.0 -8V $V_{GS} = -10V$ 0.0 -0.4 -0.6 -0.8 -1.0 -0.0 I_D, DRAIN-CURRENT (A) Fig. 6 On-Resistance vs. Drain-Current

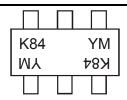


Ordering Information (Note 7)

Part Number	Case	Packaging
BSS84DW-7-F	SOT-363	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

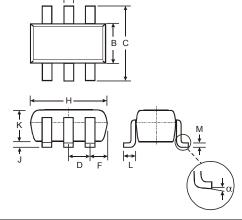


K84 = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

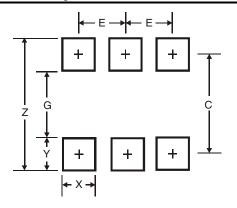
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	X	Υ	Z
Month	Jan	Fe	b	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t I	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D

Package Outline Dimensions



SOT-363						
Dim	Min	Max				
Α	0.10 0.30					
В	1.15	1.35				
C	2.00	2.20				
D	0.65 No	ominal				
F	0.30 0.40					
Н	1.80 2.20					
J	0.10					
K	0.90 1.00					
L	0.25	0.40				
М	0.10	0.25				
α	0°	8°				
All Di	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Υ	0.6
С	1.9
E	0.65

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